

LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 20 A
V_{RRM}	40 V
T_j (max)	150 °C
V_F (max)	0.49 V

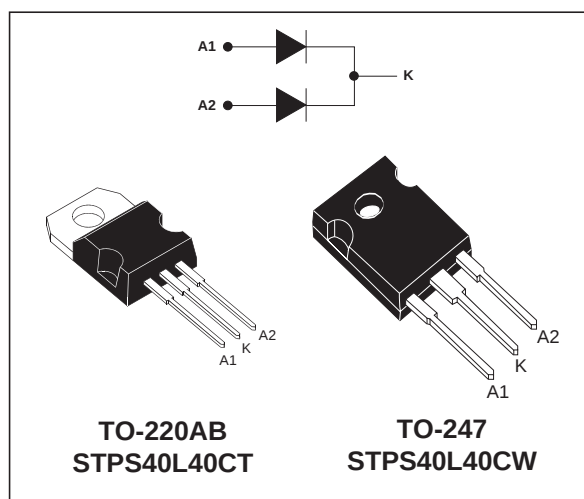
FEATURES AND BENEFITS

- LOW FORWARD VOLTAGE DROP MEANING VERY SMALL CONDUCTION LOSSES
- LOW DYNAMIC LOSSES AS A RESULT OF THE SCHOTTKY BARRIER
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tap Schottky barrier rectifier designed for high frequency Switched Mode Power Supplies and DC to DC converters.

Packaged in TO-220AB and TO-247 this device is intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			40	V
I _{F(RMS)}	RMS forward current			30	A
I _{F(AV)}	Average forward current	T _c = 130°C δ = 0.5	Per diode Per device	20 40	A
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms Sinusoidal		230	A
I _{RRM}	Repetitive peak reverse current	t _p = 2 μs square F = 1kHz		2	A
I _{RSM}	Non repetitive peak reverse current	t _p = 100 μs square		3	A
P _{ARM}	Repetitive peak avalanche power	t _p = 1μs T _j = 25°C		8100	W
T _{stg}	Storage temperature range			- 65 to + 150	°C
T _j	Maximum operating junction temperature *			150	°C
dV/dt	Critical rate of rise of reverse voltage			10000	V/μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

STPS40L40CT/CW

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.5	°C/W
		Total	0.8	
$R_{th(c)}$		Coupling	0.1	°C/W

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			0.8	mA
		$T_j = 100^\circ\text{C}$			30	70	mA
V_F^*	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 20\text{ A}$			0.53	V
		$T_j = 125^\circ\text{C}$	$I_F = 20\text{ A}$		0.42	0.49	
		$T_j = 25^\circ\text{C}$	$I_F = 40\text{ A}$			0.69	
		$T_j = 125^\circ\text{C}$	$I_F = 40\text{ A}$		0.6	0.7	

Pulse test : * $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :
 $P = 0.28 \times I_{F(AV)} + 0.0105 I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

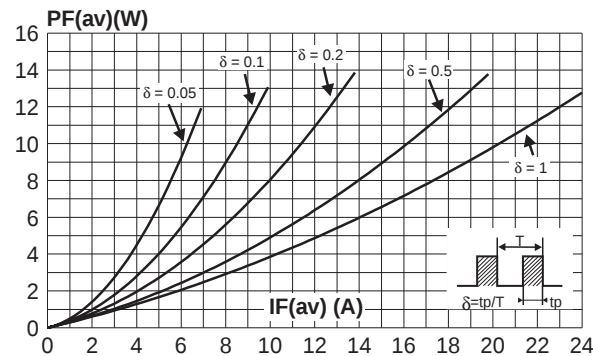


Fig. 3: Normalized avalanche power derating versus pulse duration.

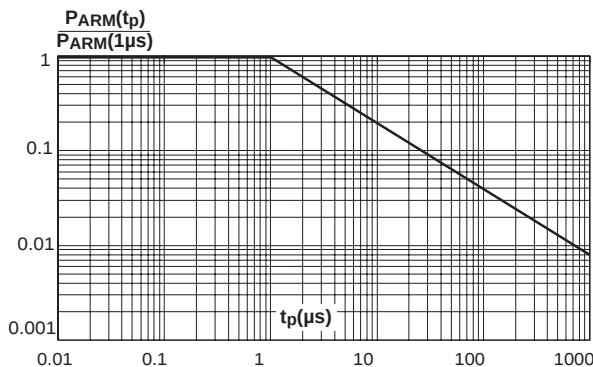


Fig. 2: Average current versus ambient temperature ($\delta = 0.5$, per diode).

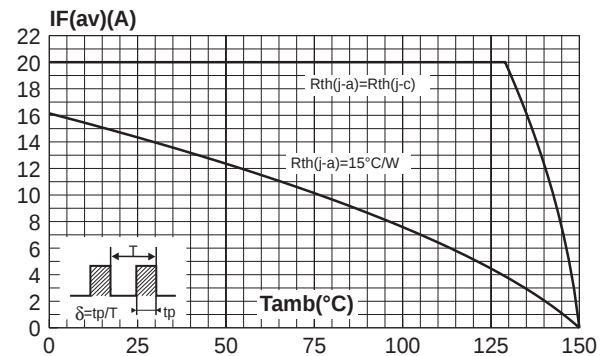


Fig. 4: Normalized avalanche power derating versus junction temperature.

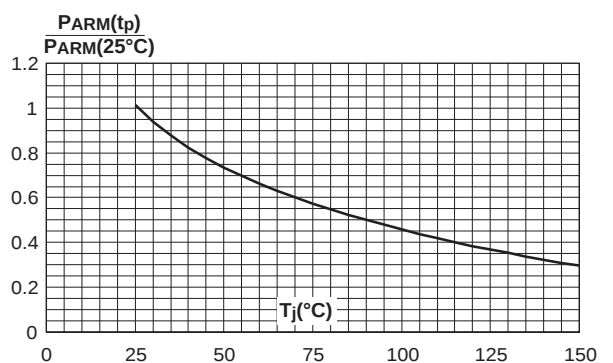


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

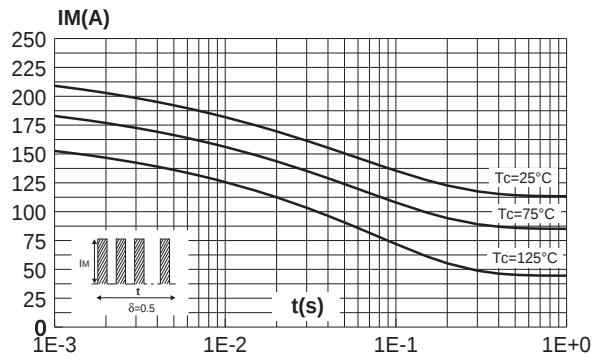


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

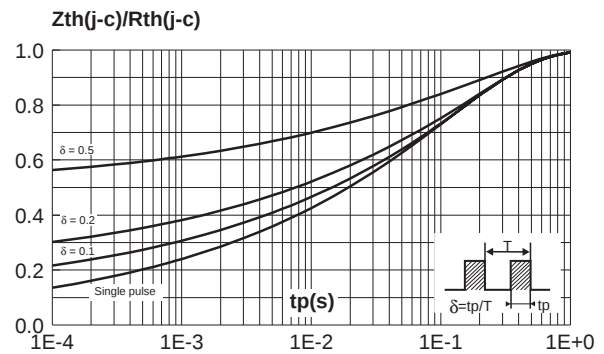


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values, per diode).

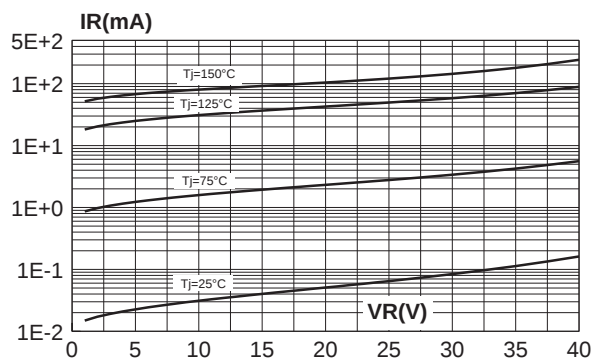


Fig. 8: Junction capacitance versus reverse voltage applied (typical values, per diode).

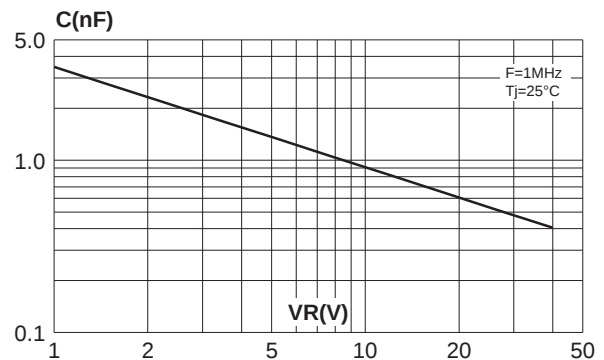
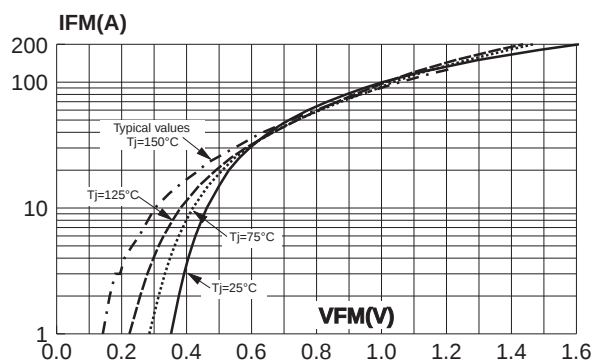
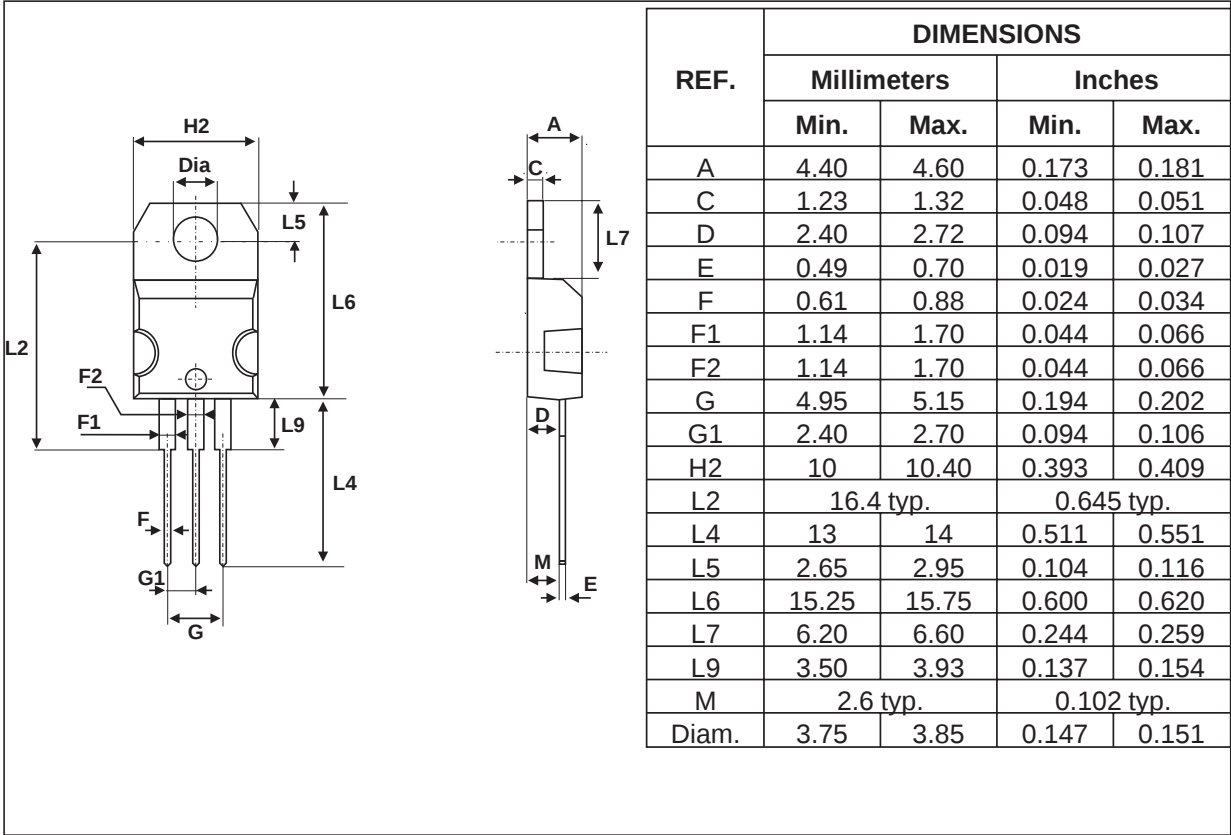


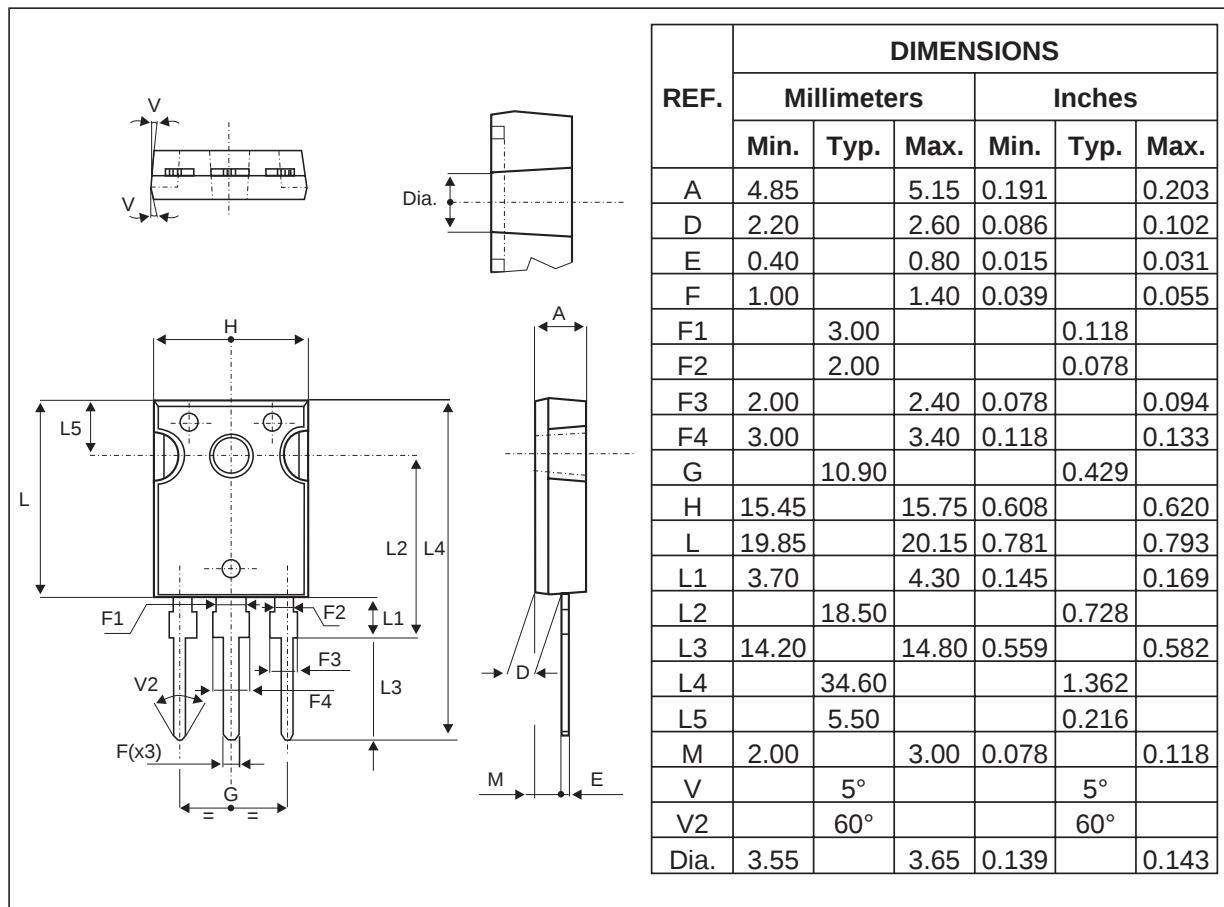
Fig. 9: Forward voltage drop versus forward current (maximum values, per diode).



PACKAGE MECHANICAL DATA
TO-220AB



- COOLING METHOD : C
- RECOMMENDED TORQUE VALUE : 0.55M.N
- MAXIMUM TORQUE VALUE : 0.70 M.N

PACKAGE MECHANICAL DATA
TO-247


- COOLING METHOD : C
- RECOMMENDED TORQUE VALUE : 0.8M.N
- MAXIMUM TORQUE VALUE : 1.0M.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS40L40CT	STPS40L40CT	TO-220AB	2g	50	Tube
STPS40L40CW	STPS40L40CW	TO-247	4.4g	30	Tube

- EPOXY MEETS UL94,V0

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